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### SNUBBERLESS™ HIGH TEMPERATURE

## 12A TRIACs

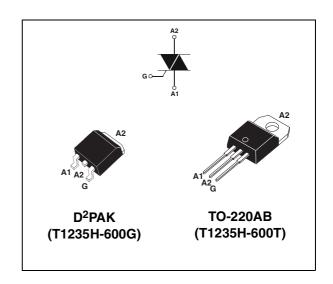
**Table 1: Main Features** 

Symbol	Value	Unit
I <sub>T(RMS)</sub>	12	Α
V <sub>DRM</sub> /V <sub>RRM</sub>	600	V
I <sub>GT (Q₁)</sub>	35	mA

### **DESCRIPTION**

Specifically designed for use in high temperature environment (found in hot appliances such as cookers, ovens, hobs, electric heaters, coffee machines...), the new 12 Amps **T1235H** triacs provide an enhanced performance in terms of power loss and thermal dissipation. This allows for optimization of the heatsinking dimensioning, leading to space and cost effectivness when compared to electro-mechnical solutions.

Based on ST snubberless technology, they offer high commutation switching capabilities and high noise immunity levels. And, thanks to their clip assembly technique, they provide a superior performance in surge current handling.



**Table 2: Order Codes** 

Part Number	Marking
T1235H-600G	T1235H600G
T1235H-600G-TR	T1235H600G
T1235H-600TRG	T1235H600T

**Table 3: Absolute Maximum Ratings** 

Symbol	Paramet	Value	Unit			
I <sub>T(RMS)</sub>	RMS on-state current (full sine wave	e)	$T_{c} = 135^{\circ}C$	12	Α	
I <sub>TSM</sub>	Non repetitive surge peak on-state	F = 50 Hz	t = 20 ms	140	Α	
'TSM	current (full cycle, $T_j$ initial = 25°C)	F = 60 Hz	t = 16.7 ms	145		
l <sup>2</sup> t	l <sup>2</sup> t Value for fusing	t <sub>p</sub> = 10 ms		112	A <sup>2</sup> s	
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ , $t_r \le 100 \text{ ns}$	F = 120 Hz	T <sub>j</sub> = 150°C	50	A/µs	
V <sub>DSM</sub> /V <sub>RSM</sub>	Non repetitive surge peak off-state voltage	t <sub>p</sub> = 10 ms	T <sub>j</sub> = 25°C	700	V	
I <sub>GM</sub>	Peak gate current $t_p = 20 \mu s$ $T_j = 150^{\circ} C$		$T_j = 150^{\circ}C$	4	Α	
P <sub>G(AV)</sub>	Average gate power dissipation $T_j = 150^{\circ}C$		1	W		
T <sub>stg</sub> T <sub>j</sub>	Storage junction temperature range Operating junction temperature range			- 40 to + 150 - 40 to + 150	°C	

**Tables 4: Electrical Characteristics** ( $T_j = 25$ °C, unless otherwise specified)

Symbol	Test Conditions	Quadrant		Value	Unit
I <sub>GT</sub> (1)	$V_D = 12 \text{ V}  R_L = 33 \Omega$	1 - 11 - 111	MAX.	35	mA
V <sub>GT</sub>	VD = 12 V 11[ = 00 32	1 - 11 - 111	MAX.	1.3	V
$V_{GD}$	$V_D = V_{DRM}$ $R_L = 3.3 \text{ k}\Omega$ $T_j = 150^{\circ}\text{C}$ I - II - III		MIN.	0.15	V
I <sub>H</sub> (2)	I <sub>T</sub> = 100 mA		MAX.	35	mA
IL	$I_{L}$ $I_{G} = 1.2 I_{GT}$		MAX.	50	mA
'L	- G - 1.2 ·G1	II	WIAX.	80	ША
dV/dt (2)	$V_D = 67 \text{ %}V_{DRM} \text{ gate open } T_j = 150 ^{\circ}\text{C}$		MIN.	300	V/µs
(dl/dt)c (2)	Without snubber $T_j = 150^{\circ}C$		MIN.	5.3	A/ms

**Table 5: Static Characteristics** 

Symbol	Test C	Value	Unit		
V <sub>T</sub> (2)	$I_{TM} = 17 \text{ A}$ $t_p = 380  \mu\text{s}$	T <sub>j</sub> = 25°C	MAX.	1.55	V
V <sub>to</sub> (2)	Threshold voltage	T <sub>j</sub> = 150°C	MAX.	0.80	V
R <sub>d</sub> (2)	Dynamic resistance	T <sub>j</sub> = 150°C	MAX.	25	mΩ
	$V_{DRM} = V_{RRM}$	T <sub>j</sub> = 25°C		5	μΑ
I <sub>DRM</sub>	VDRM — VRRM	T <sub>j</sub> = 150°C	MAX.	5.5	
IRRM	V <sub>DRM</sub> /V <sub>RRM</sub> = 400V (at mains peak voltage)	T <sub>j</sub> = 150°C		3.5	mA

Note 1: minimum I<sub>GT</sub> is guaranted at 10% of I<sub>GT</sub> max. Note 2: for both polarities of A2 referenced to A1.

**Table 6: Thermal resistance** 

Symbol	Parameter			Value	Unit
R <sub>th(j-c)</sub>	Junction to case (AC)		D <sup>2</sup> PAK	1.2	°C/W
' 'th(j-c)	Junction to case (AC)		TO-220AB	1.2	C/VV
R <sub>th(j-a)</sub>	Junction to ambient	$S = 1 \text{ cm}^2$	D <sup>2</sup> PAK	45	°C/W
' 'th(j-a)			TO-220AB	60	O/ VV

S = Copper surface under tab.

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Figure 1: Maximum power dissipation versus RMS on-state current (full cycle)

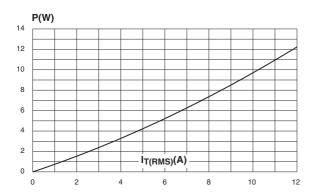


Figure 3: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness: 35µm) (full cycle)

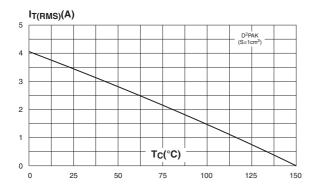


Figure 5: On-state characteristics (maximum values)

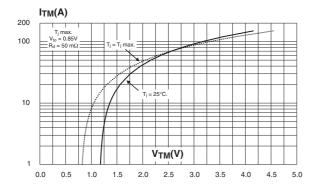


Figure 2: RMS on-state current versus case temperature (full cycle)

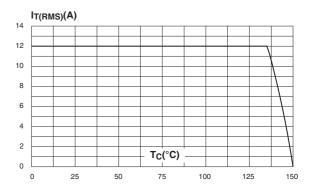


Figure 4: Relative variation of thermal impedance versus pulse duration

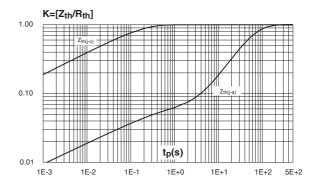


Figure 6: Surge peak on-state current versus number of cycles

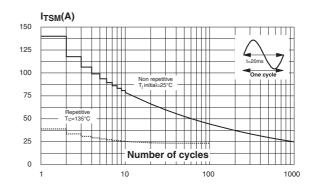


Figure 7: Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_{\rm p}$  < 10 ms and corresponding value of  $l^2t$ 

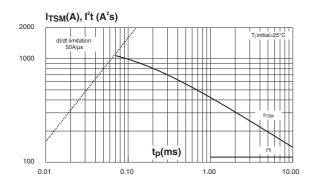


Figure 9: Relative variation of critical rate of decrease of main current versus (dV/dt)c (typical values)

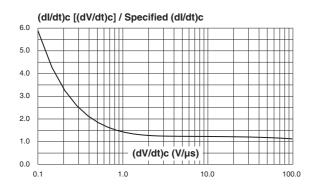


Figure 11: Leakage current versus junction temperature for different values of blocking voltage (typical values)

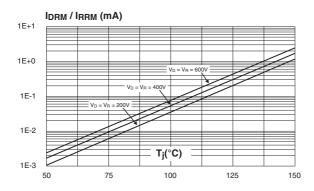


Figure 8: Relative variation of gate trigger current, holding current and latching current versus junction temperature (typical values)

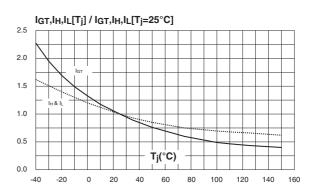


Figure 10: Relative variation of critical rate of decrease of main current versus junction temperature

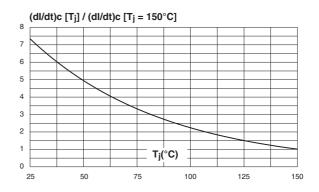
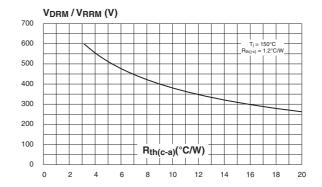


Figure 12: Acceptable repetitive peak off-state voltage versus case-ambient thermal resistance



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Figure 13: D<sup>2</sup>PAK Thermal resistance junction to ambient versus copper surface under tab (printed circuit board FR4, copper thickness: 35 μm)

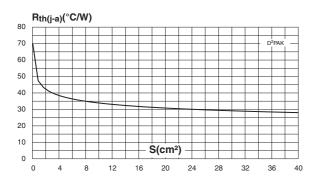
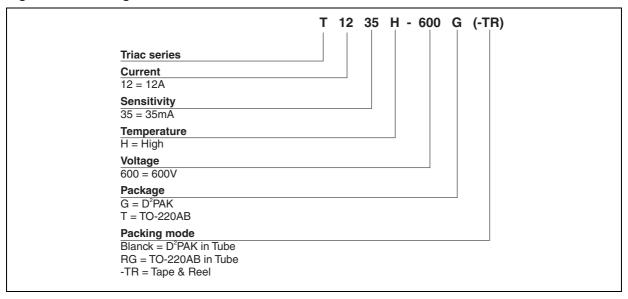


Figure 14: Ordering Information Scheme



**Table 7: Product Selector** 

Part Numbers	Voltage	Sensitivity	Туре	Package
T1235H-600G	600 V	35 mA	Snubberless	D <sup>2</sup> PAK
T1235H-600T	600 V	35 mA	Snubberless	TO-220AB

Figure 15: D<sup>2</sup>PAK Package Mechanical Data

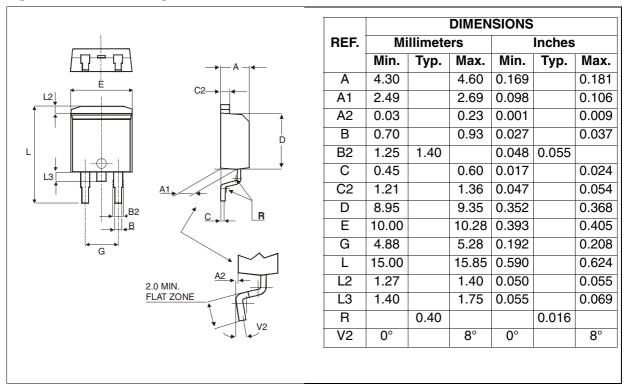
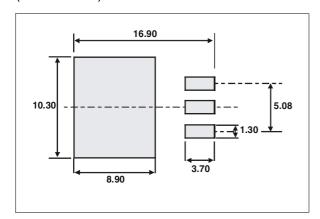


Figure 16: D<sup>2</sup>PAK Foot Print Dimensions (in millimeters)



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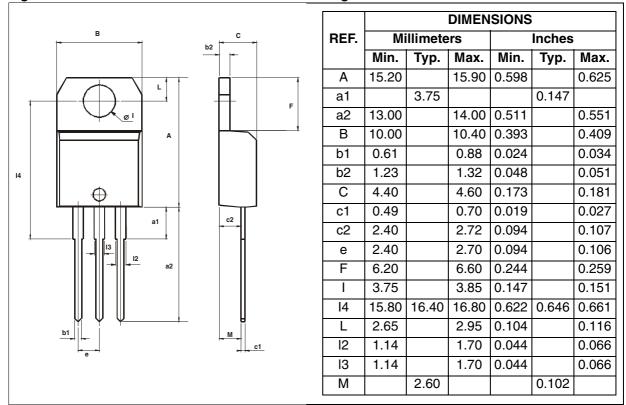


Figure 17: TO-220AB and TO-220AB Insulated Package Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: <a href="https://www.st.com">www.st.com</a>.

**Table 8: Ordering Information** 

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
T1235H-600TRG	T1235H600T	TO-220AB	2.3 g	50	Tube
T1235H-600G	T1235H600G	D <sup>2</sup> PAK	1.5 g	50	Tube
T1235H-600G-TR	T1235H600G	D-FAR	1.5 g	1000	Tape & reel

**Table 9: Revision History** 

Date	Revision	Description of Changes
Apr-2002	5A	Last update.
13-Feb-2006	6	TO-220AB delivery mode changed from bulk to tube. ECOPACK statement added.

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